

2N3055A (NPN), MJ15015 (NPN), MJ15016 (PNP)

MJ15015 and MJ15016 are Preferred Devices

Complementary Silicon High-Power Transistors

These PowerBase™ complementary transistors are designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc-to-dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055.

Features

- Current-Gain – Bandwidth-Product @ $I_C = 1.0 \text{ A dc}$
 $f_T = 0.8 \text{ MHz (Min) – NPN}$
 $= 2.2 \text{ MHz (Min) – PNP}$
- Safe Operating Area – Rated to 60 V and 120 V, Respectively
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage 2N3055A MJ15015, MJ15016	V_{CEO}	60 120	Vdc
Collector-Base Voltage 2N3055A MJ15015, MJ15016	V_{CBO}	100 200	Vdc
Collector-Emitter Voltage Base Reversed Biased 2N3055A MJ15015, MJ15016	V_{CEV}	100 200	Vdc
Emitter-Base Voltage	V_{EBO}	7.0	Vdc
Collector Current – Continuous	I_C	15	Adc
Base Current	I_B	7.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C 2N3055A	P_D	115 0.65	W W/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C MJ15015, MJ15016		180 1.03	
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.52	0.98	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data. (2N3055A)

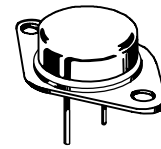
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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**15 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
60, 120 VOLTS – 115, 180 WATTS**



**TO-204AA (TO-3)
CASE 1-07
STYLE 1**

MARKING DIAGRAMS



2N3055A = Device Code
MJ1501x = Device Code
x = 5 or 6
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS (Note 2)

Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 200\text{ mAdc}$, $I_B = 0$)	2N3055A MJ15015, MJ15016	$V_{CEO(sus)}$	60 120	– –	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{BE(off)} = 0\text{ Vdc}$) ($V_{CE} = 60\text{ Vdc}$, $V_{BE(off)} = 0\text{ Vdc}$)	2N3055A MJ15015, MJ15016	I_{CEO}	– –	0.7 0.1	mAdc
Collector Cutoff Current (Note 3) ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$)	2N3055A MJ15015, MJ15016	I_{CEV}	– –	5.0 1.0	mAdc
Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$)	2N3055A MJ15015, MJ15016	I_{CEV}	– –	30 6.0	mAdc
Emitter Cutoff Current ($V_{EB} = 7.0\text{ Vdc}$, $I_C = 0$)	2N3055A MJ15015, MJ15016	I_{EBO}	– –	5.0 0.2	mAdc

SECOND BREAKDOWN (Note 3)

Second Breakdown Collector Current with Base Forward Biased ($t = 0.5\text{ s non-repetitive}$) ($V_{CE} = 60\text{ Vdc}$)	2N3055A MJ15015, MJ15016	$I_{S/b}$	1.95 3.0	– –	Adc
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ON CHARACTERISTICS (Note 2 and 3)

DC Current Gain ($I_C = 4.0\text{ Adc}$, $V_{CE} = 2.0\text{ Vdc}$) ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 10\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	10 20 5.0	70 70 –	–
Collector-Emitter Saturation Voltage ($I_C = 4.0\text{ Adc}$, $I_B = 400\text{ mAdc}$) ($I_C = 10\text{ Adc}$, $I_B = 3.3\text{ Adc}$) ($I_C = 15\text{ Adc}$, $I_B = 7.0\text{ Adc}$)	$V_{CE(sat)}$	– – –	1.1 3.0 5.0	Vdc
Base-Emitter On Voltage ($I_C = 4.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	0.7	1.8	Vdc

DYNAMIC CHARACTERISTICS (Note 3)

Current-Gain – Bandwidth Product ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	2N3055A, MJ15015 MJ15016	f_T	0.8 2.2	6.0 18	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{ob}	60	600	pF

SWITCHING CHARACTERISTICS (2N3055A only) (Note 3)

RESISTIVE LOAD					
Delay Time	(V _{CC} = 30 Vdc, I _C = 4.0 Adc, I _{B1} = I _{B2} = 0.4 Adc, t _p = 25 μs Duty Cycle ≤ 2%)	t _d	–	0.5	μs
Rise Time		t _r	–	4.0	μs
Storage Time		t _s	–	3.0	μs
Fall Time		t _f	–	6.0	μs

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

3. Indicates JEDEC Registered Data. (2N3055A)

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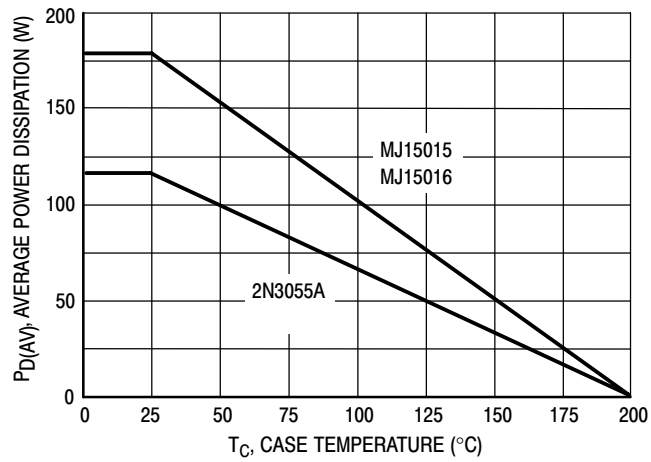


Figure 1. Power Derating

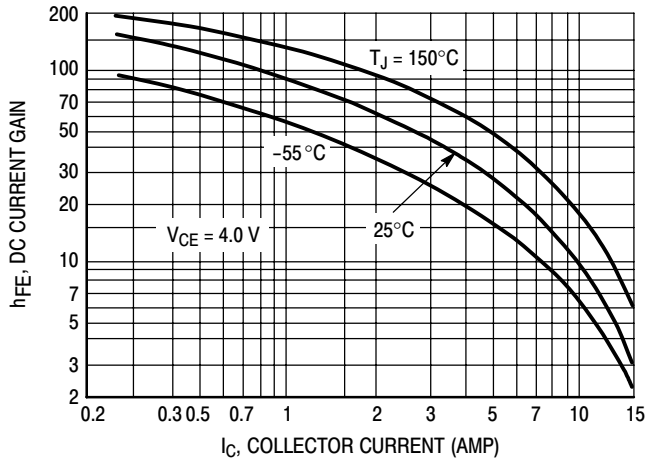


Figure 2. DC Current Gain

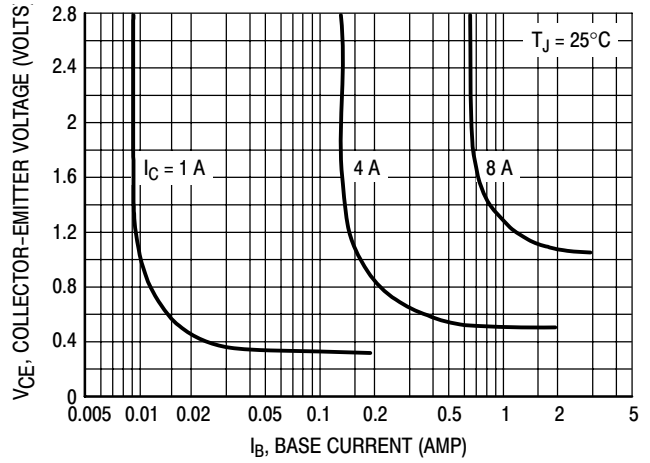


Figure 3. Collector Saturation Region

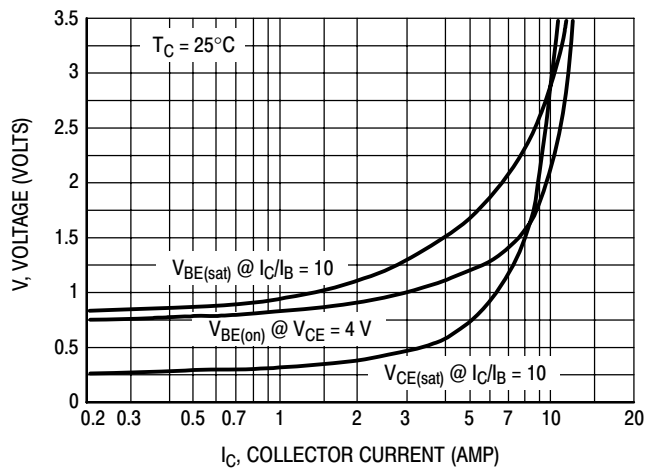


Figure 4. "On" Voltages

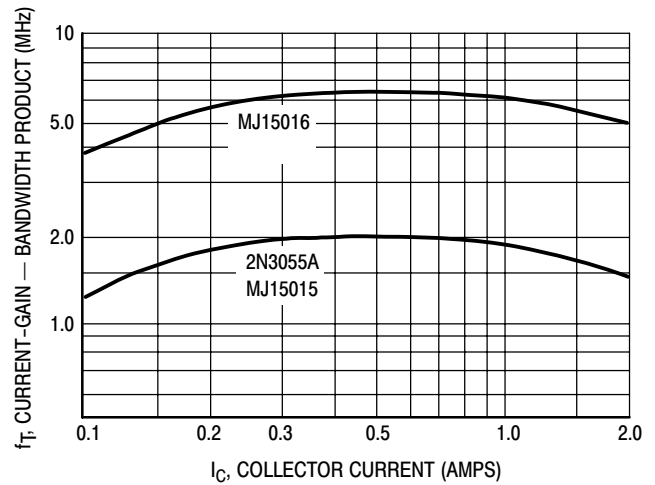


Figure 5. Current-Gain — Bandwidth Product

2N3055A (NPN), MJ15015 (NPN), MJ15016 (PNP)

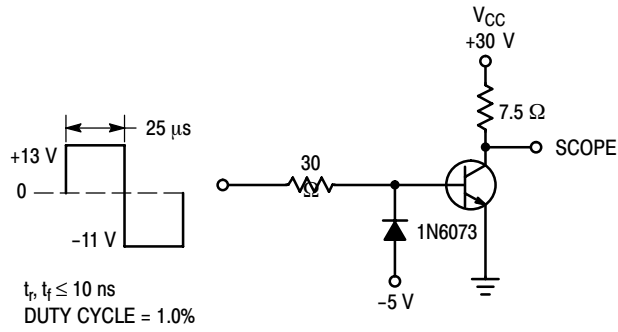


Figure 6. Switching Times Test Circuit
(Circuit shown is for NPN)

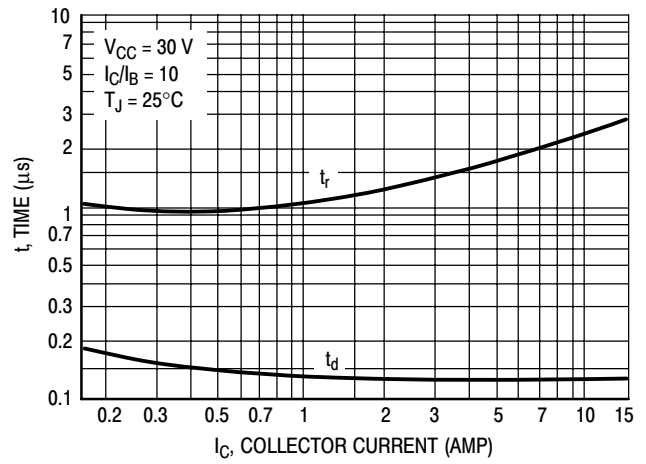


Figure 7. Turn-On Time

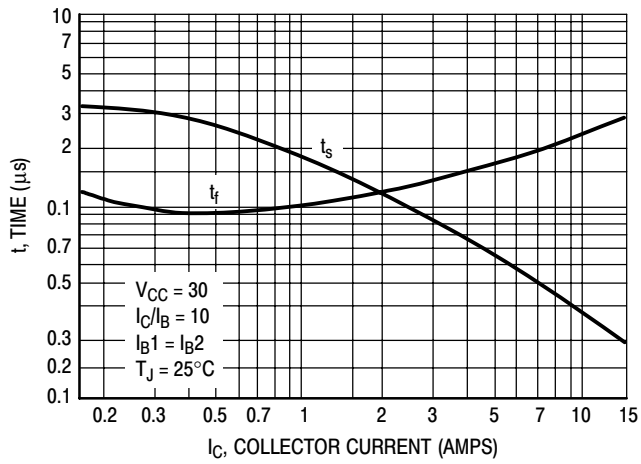


Figure 8. Turn-Off Times

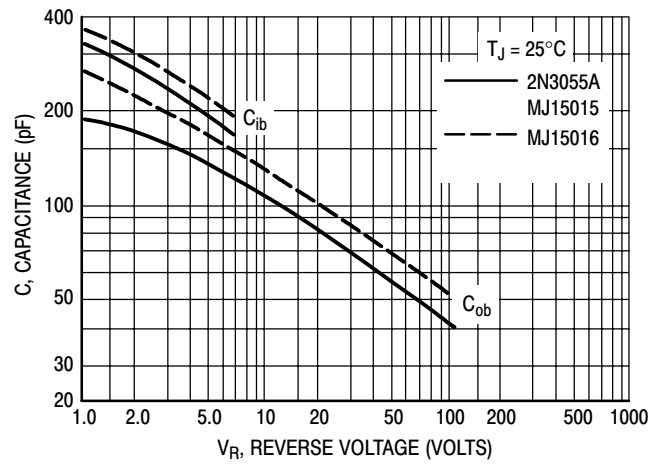


Figure 9. Capacitances

2N3055A (NPN), MJ15015 (NPN), MJ15016 (PNP)

COLLECTOR CUT-OFF REGION

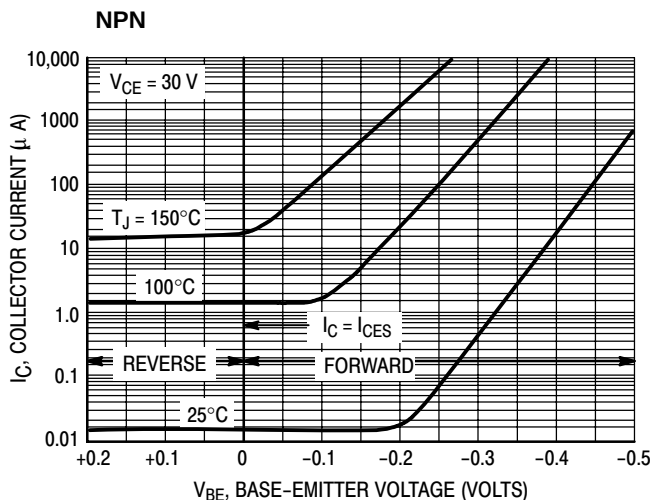


Figure 10. 2N3055A, MJ15015

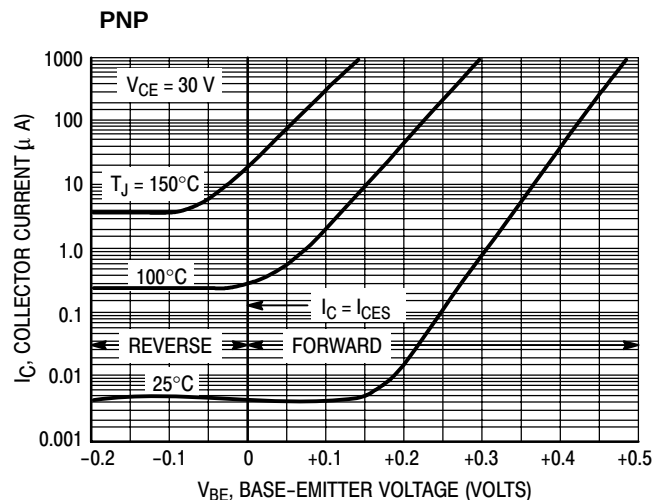


Figure 11. MJ15016

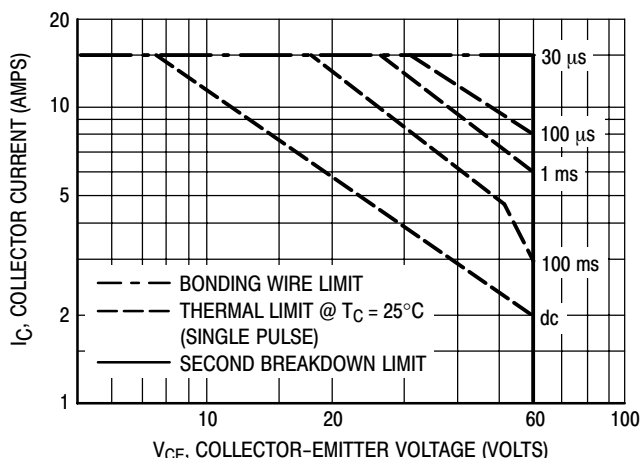


Figure 12. Forward Bias Safe Operating Area
2N3055A

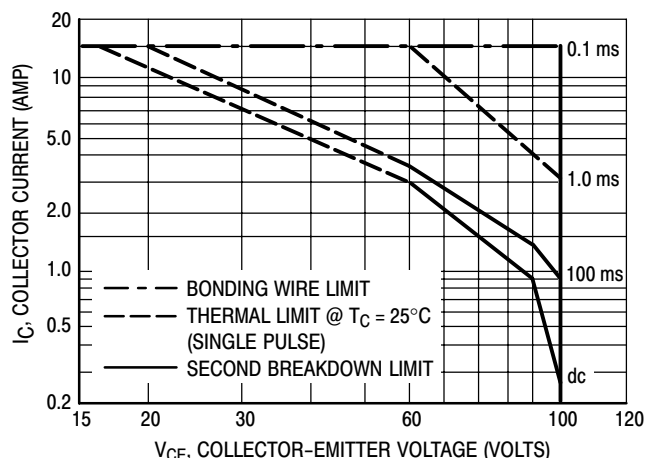


Figure 13. Forward Bias Safe Operating Area
MJ15015, MJ15016

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 12 and 13 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

ORDERING INFORMATION

Device	Package	Shipping
2N3055A	TO-204	100 Units / Tray
2N3055AG	TO-204 (Pb-Free)	
MJ15015	TO-204	100 Units / Tray
MJ15015G	TO-204 (Pb-Free)	
MJ15016	TO-204	
MJ15016G	TO-204 (Pb-Free)	



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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